

ABSTRACT OF THE DISCLOSURE

A dielectric device having excellent characteristics is provided. This dielectric device comprises such a first electrode layer that constituent elements located on its surface are terminated by halogen atoms and a dielectric film formed on the surface of the first electrode layer terminated by the halogen atoms. When the constituent elements for the first electrode layer located on the surface thereof are terminated by the halogen atoms in order to form a ferroelectric film having a bismuth layer structure, therefore, Bi constituting the ferroelectric film is inhibited from bonding to the constituent elements located on the surface of the first electrode layer.